# 2SC6094

# ON Semiconductor®

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# **Bipolar Transistor** 60V, 3A, Low VCE(sat), NPN Single PCP

## **Applications**

• DC / DC converter, relay drivers, lamp drivers, motor drivers, inverter

#### **Features**

- · Adoption of FBET, MBIT process
- Low collector-to-emitter saturation voltage
- · High allowable power dissipation

- · Large current capacity
- · High-speed switching

### **Specifications**

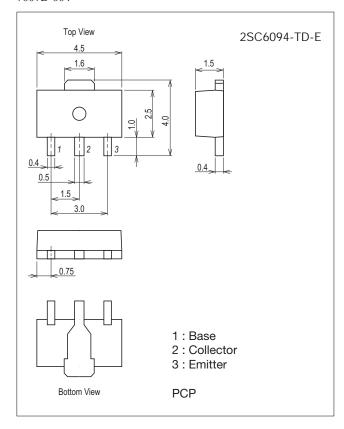
#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		100	V
Collector-to-Emitter Voltage	VCES		100	V
	VCEO		60	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		6.5	V
Collector Current	IC		3	Α
Collector Current (Pulse)	ICP		5	А

Continued on next page.

#### **Package Dimensions**

unit: mm (typ) 7007B-004



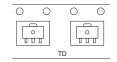
## **Product & Package Information**

• Package : PCP

• JEITA, JEDEC : SC-62, SOT-89, TO-243

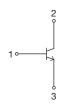
• Minimum Packing Quantity: 1,000 pcs./reel

#### Packing Type: TD Marking





#### **Electrical Connection**



#### Continued from preceding page.

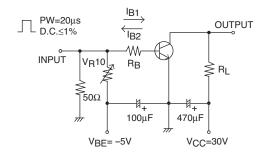
Parameter	Symbol	Conditions	Ratings	Unit
Base Current	IB		600	mA
Collector Dissipation	I Pc	When mounted on ceramic substrate (250mm <sup>2</sup> ×0.8mm)	1.3	W
		Tc=25°C	3.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

#### Electrical Characteristics at Ta=25°C

Parameter	Cumbal	Conditions	Ratings			Linit
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector Cutoff Current	ICBO	V <sub>CB</sub> =50V, I <sub>E</sub> =0A			1	μΑ
Emitter Cutoff Current	IEBO	V <sub>EB</sub> =4V, I <sub>C</sub> =0A			1	μΑ
DC Current Gain	hFE	V <sub>CE</sub> =2V, I <sub>C</sub> =100mA	300		600	
Gain-Bandwidth Product	fŢ	V <sub>CE</sub> =10V, I <sub>C</sub> =500mA		390		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		18		pF
Collector-to-Emitter Saturation Voltage	V <sub>CE</sub> (sat)1	I <sub>C</sub> =1A, I <sub>B</sub> =50mA		90	135	mV
	V <sub>CE</sub> (sat)2	I <sub>C</sub> =1A, I <sub>B</sub> =100mA		80	120	mV
Base-to-Emitter Saturation Voltage	VBE(sat)	IC=1A, IB=100mA		0.84	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I <sub>C</sub> =10μA, I <sub>E</sub> =0A	100			V
Collector-to-Emitter Breakdown Voltage	V(BR)CES	I <sub>C</sub> =100μA, R <sub>BE</sub> =0Ω	100			V
	V(BR)CEO	IC=1mA, RBE=∞	60			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =10μA, I <sub>C</sub> =0A	6.5			V
Turn-ON Time	ton			35		ns
Storage Time	t <sub>stg</sub>	See specified Test Circuit.		680		ns
Fall Time	tf			24		ns

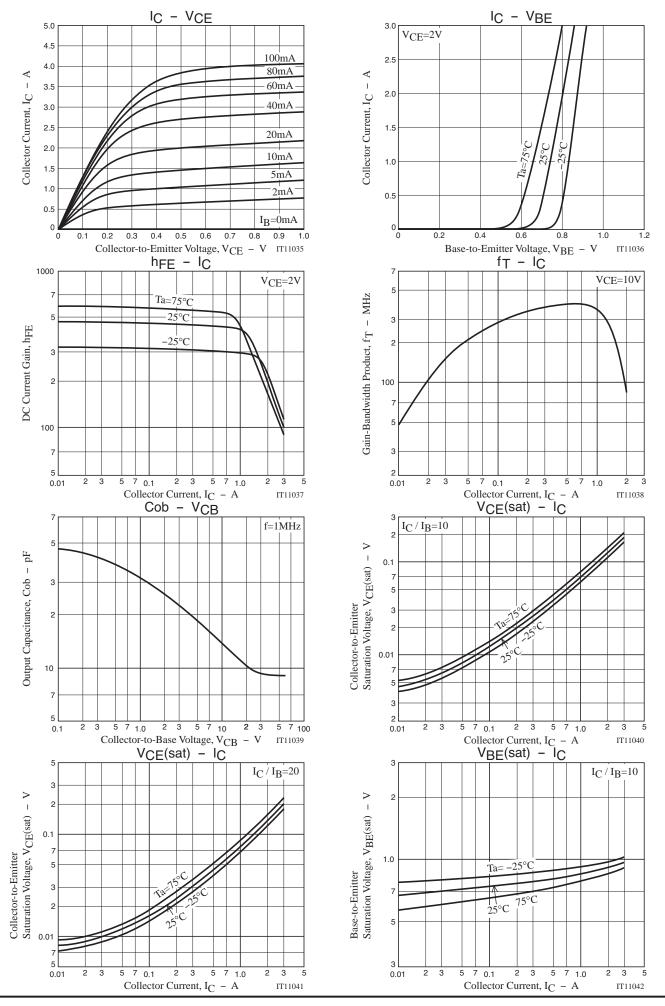
# **Switching Time Test Circuit**

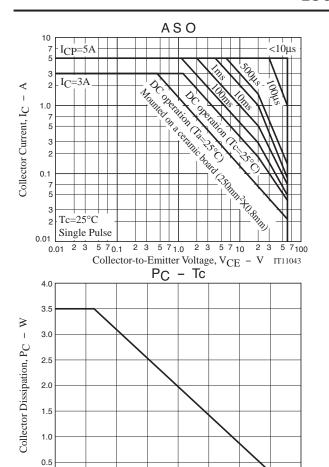


 $I_{C}=10I_{B1}=-10I_{B2}=0.5A$ 

## **Ordering Information**

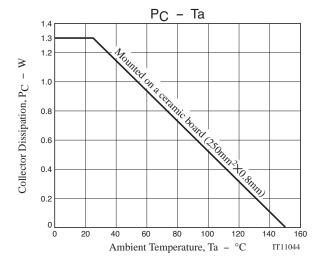
Device	Device Package		memo	
2SC6094-TD-E PCP		1,000pcs./reel	Pb Free	





Case Temperature, Tc  $\,$  -  $\,$   $^{\circ}$ C

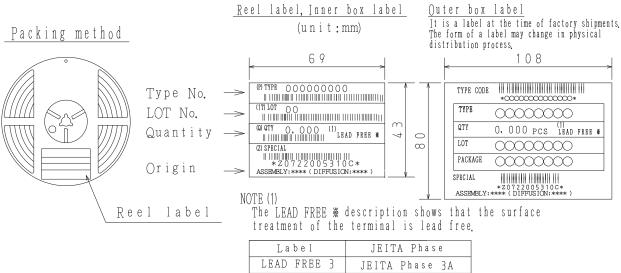
IT11045



# Embossed Taping Specification 2SC6094-TD-E

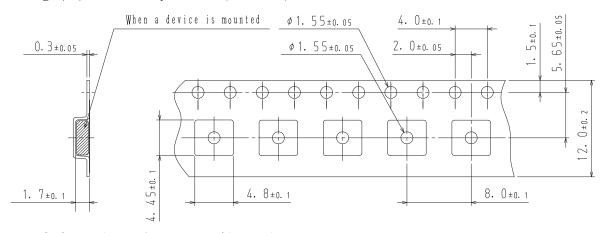
# 1. Packing Format

Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing	ing format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)		
PCP	PCP	1, 000	4,000	24, 000	4 reels contained	6 inner boxes contained		
					Dimensions:mm (external)	Dimensions:mm (external)		
					183×72×185	440×195×210		



# 2. Taping configuration

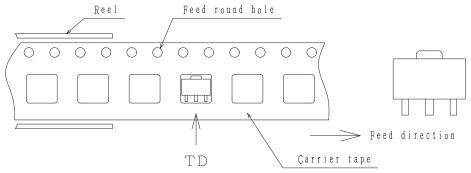
2-1. Carrier tape size (unit:mm)



LEAD FREE 4

JEITA Phase 3

2-2. Device placement direction



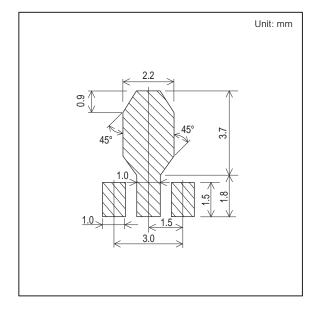
Those with pin 1 index on the feed hole side·····TD

# **Outline Drawing**

2SC6094-TD-E

# Mass (g) Unit 0.058 For reference mm 4. 5±0. 1 1. 6±0. 2 \_ 1.5±0.1\_ 2. 5±0. 1 4. 0±0. 2 1. 0±0. 2 0. 4+0. 08 0. 4±0. 03 0. 5<sup>+0. 05</sup> 1. 5±0. 2 3. O±0. 2 0. 75 0.10 \*1:Lot indication

## **Land Pattern Example**



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